EB13C3F2H-16.000M

Storage Temperature Range



Nominal Frequency

16.000MHz

Logic Control / Additional Output

Tri-State (High Impedance)

EB13C3 F 2 H -16.000M

Series -RoHS Compliant (Pb-free) Low Current 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability ±20ppm over 0°C to +70°C

Duty Cycle -50 ±5(%)

ELECTRICAL SPECIFICATIONS			
Nominal Frequency	16.000MHz		
Frequency Tolerance/Stability	±20ppm over 0°C to +70°C (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration)		
Supply Voltage	3.3Vdc ±10%		
Input Current	3mA Maximum		
Output Voltage Logic High (Voh)	90% of Vdd Minimum		
Input Current Logic High (Ioh)	-1.6mA		
Output Voltage Logic Low (Vol)	10% of Vdd Maximum		
Input Current Logic Low (IoI)	+1.6mA		
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)		
Duty Cycle	50 \pm 5(%) (Measured at 50% of waveform)		
Load Drive Capability	15pF Maximum		
Output Logic Type	CMOS		
Logic Control / Additional Output	Tri-State (High Impedance)		
Tri-State Input Voltage (Vih and Vil)	90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)		
Standby Current	10µA Maximum (Disabled Output: High Impedance)		
One Sigma Clock Period Jitter	25pSec Maximum		
Start Up Time	10mSec Maximum		

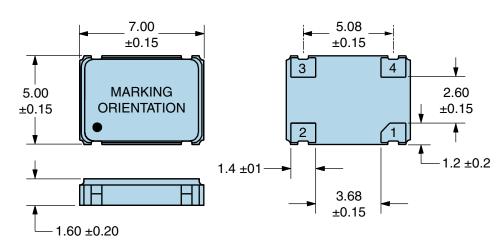
ENVIRONMENTAL & MECHANICAL SPECIFICATIONS Fine Leak Test MIL-STD-883, Method 1014, Condition A Gross Leak Test MIL-STD-883, Method 1014, Condition C

-55°C to +125°C

Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007, Condition A

EB13C3F2H-16.000M

MECHANICAL DIMENSIONS (all dimensions in millimeters)

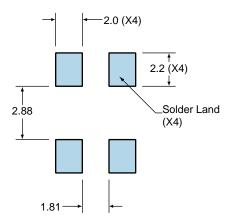


EC	LIP	TEK®
COR	RPOR/	ATION

PIN	CONNECTION
1	Tri-State
2 3	Ground
3	Output
4	Supply Voltage
LINE	MARKING
1	ECLIPTEK
2	16.000M
3	XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

Suggested Solder Pad Layout

All Dimensions in Millimeters

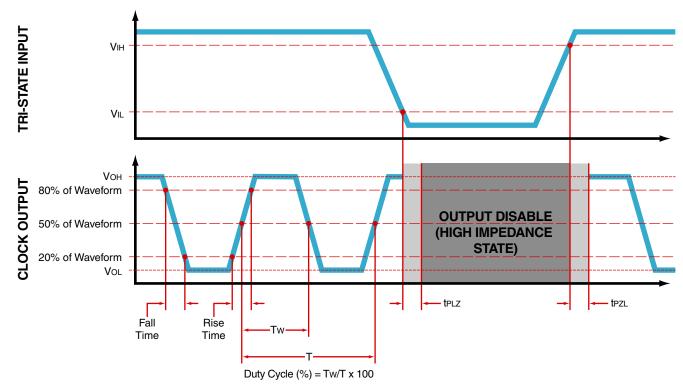


All Tolerances are ±0.1

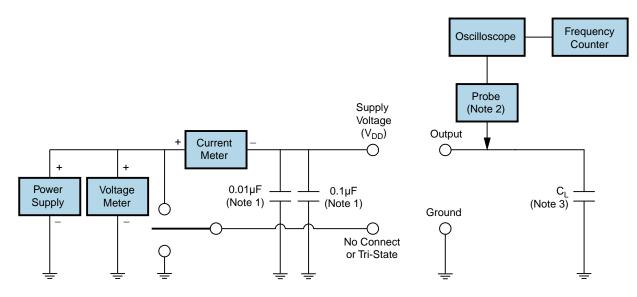
EB13C3F2H-16.000M



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



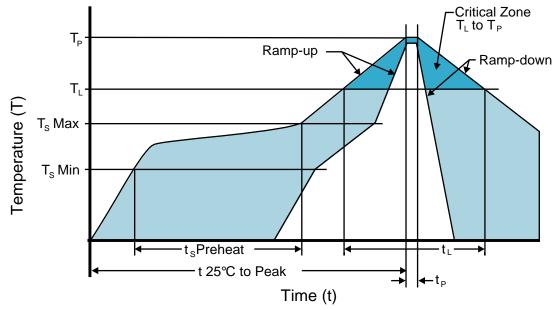
Note 1: An external 0.1μ F low frequency tantalum bypass capacitor in parallel with a 0.01μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

EB13C3F2H-16.000M

<u> </u>	
T _s MAX to T _L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
 Temperature Maximum (T_s MAX) 	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T⊾ to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _P)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods

EB13C3F2H-16.000M



Low Temperature Infrared/Convection 240°C

T _s MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
 Temperature Typical (T_s TYP) 	150°C
 Temperature Maximum (T_s MAX) 	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t _P)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)